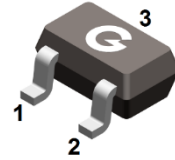
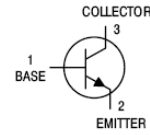


Features

- Epitaxial planar die construction
- Complimentary to MMST4403
- Ultra-small surface mount package

HF



SOT-323

Mechanical Data

- Case: SOT-323
- Molding compound: UL flammability classification rating 94V-0
- Terminals: Tin-plated; solderability per MIL-STD-202, Method 208

Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
MMST4401	SOT-323	3000 pcs / Tape & Reel	K3X

Maximum Ratings (@ T_A = 25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Collector-Base Breakdown Voltage	V _{CBO}	60	V
Collector-Emitter Breakdown Voltage	V _{CEO}	40	V
Emitter-Base Breakdown Voltage	V _{EBO}	6	V
Collector Current (Continuous)	I _C	0.6	A
Collector Current (Peak)	I _{CM}	0.8	A

Thermal Characteristics

Parameter	Symbol	Value	Unit
Power Dissipation *1	P _D	0.2	W
Thermal Resistance Junction-to-Air *1	R _{θJA}	625	°C/W
Thermal Resistance Junction-to-Air *2	R _{θJA}	252	°C/W
Thermal Resistance Junction-to-Case *2	R _{θJC}	147	°C/W
Thermal Resistance Junction-to-Lead *2	R _{θJL}	174	°C/W
Junction Temperature	T _J	-55 ~ +150	°C
Storage Temperature Range	T _{STG}	-55 ~ +150	°C

Notes:

1. Device mounted on a minimum recommended pad layout with 1oz copper that is on a single-sided 1.6mm FR4 PCB; the device is measured under still air conditions whilst operating in a steady-state.
2. The data tested by surface mounted on a 25.4mm * 25.4mm * 1mm FR4-epoxy P.C.B

Electrical Characteristics (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symb ol	Test Condition	Min.	Typ.	Max .	Unit
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 100\mu\text{A}$, $I_E = 0$	60	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 1\text{mA}$, $I_B = 0$	40	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 100\mu\text{A}$, $I_C = 0$	6	-	-	V
Collector Cut-off Current	I_{CEX}	$V_{CE} = 35\text{V}$, $V_{EB(OFF)} = 0.4\text{V}$	-	-	100	nA
Base Cut-off Current	I_{BL}	$V_{CE} = 35\text{V}$, $V_{EB(OFF)} = 0.4\text{V}$	-	-	100	nA
DC Current Gain	h_{FE}	$V_{CE} = 1\text{V}$, $I_C = 0.1\text{mA}$	20	-	-	-
		$V_{CE} = 1\text{V}$, $I_C = 1\text{mA}$	40	-	-	-
		$V_{CE} = 1\text{V}$, $I_C = 10\text{mA}$	80	-	-	-
		$V_{CE} = 1\text{V}$, $I_C = 150\text{mA}$	100	-	300	-
		$V_{CE} = 2\text{V}$, $I_C = 500\text{mA}$	40	-	-	-
Collector-emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 500\text{mA}$, $I_B = 50\text{mA}$	-	-	0.75	V
		$I_C = 150\text{mA}$, $I_B = 15\text{mA}$	-	-	0.4	V
Base-emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 500\text{mA}$, $I_B = 50\text{mA}$	-	-	1.2	V
		$I_C = 150\text{mA}$, $I_B = 15\text{mA}$	-	-	0.95	V
Transition Frequency	f_T	$I_C = 20\text{mA}$, $V_{CE} = 10\text{V}$, $f = 100\text{MHz}$	250	-	-	MHz
Collector Output Capacitance	C_{OBO}	$V_{CB} = 5\text{V}$, $I_E = 0$, $f = 1\text{MHz}$	-	-	6.5	pF
Delay Time	t_d	$V_{CC} = 30\text{V}$, $I_C = 150\text{mA}$	-	-	15	ns
Rise Time	t_r	$V_{BE(OFF)} = 2\text{V}$, $I_{B1} = 15\text{mA}$	-	-	20	ns
Storage Time	t_s	$V_{CC} = 30\text{V}$, $I_C = 150\text{mA}$	-	-	225	ns
Fall Time	t_f	$I_{B1} = I_{B2} = 15\text{mA}$	-	-	30	ns

Ratings and Characteristics Curves (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

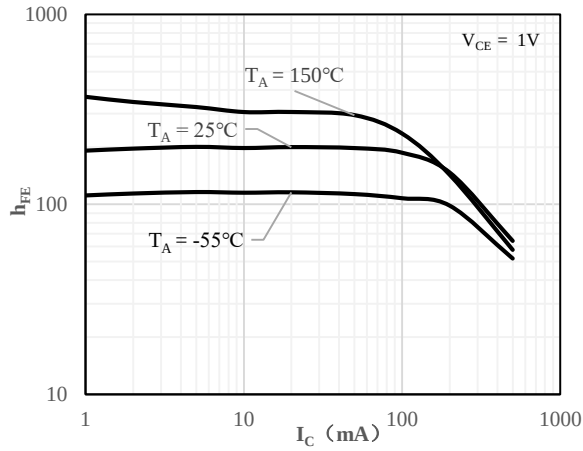


Fig 1 h_{FE} vs. I_C

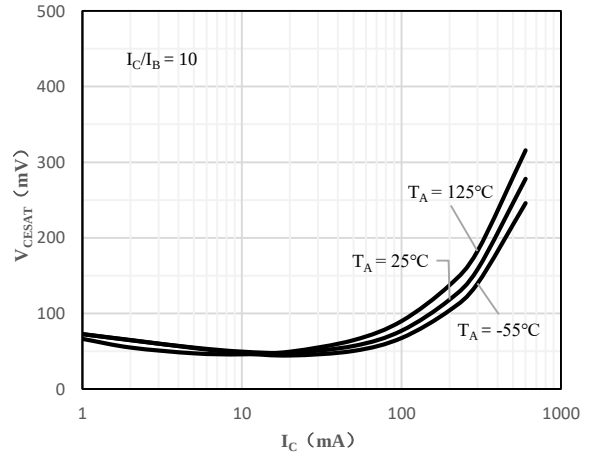


Fig 2 $V_{CE(sat)}$ vs. I_C

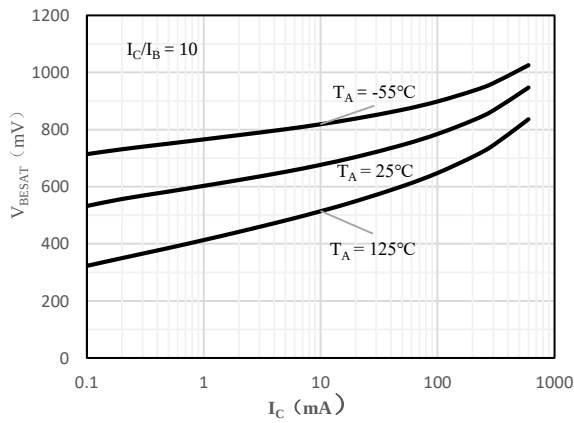


Fig 3 $V_{BE(sat)}$ vs. I_C

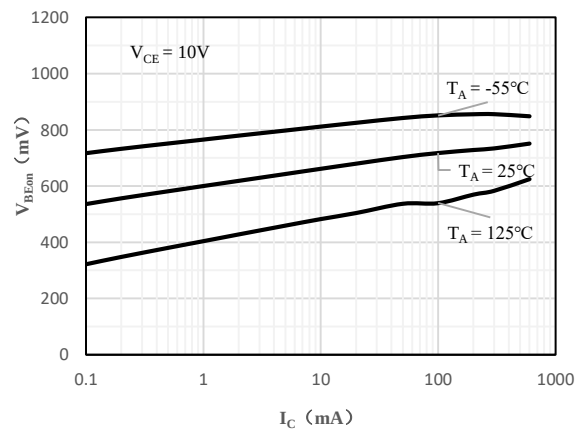
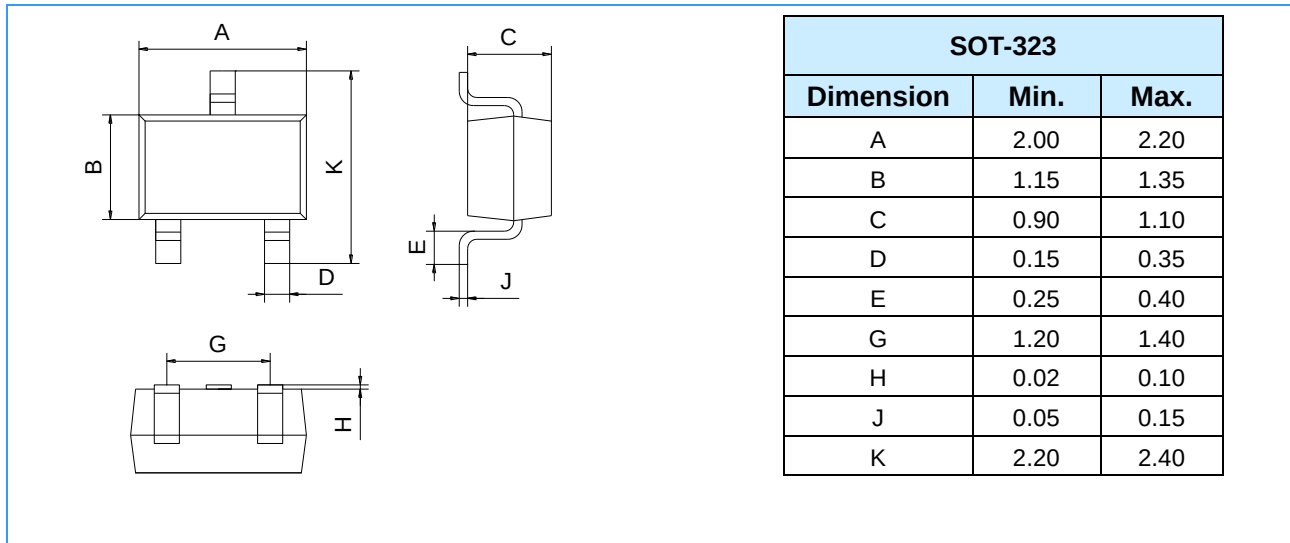
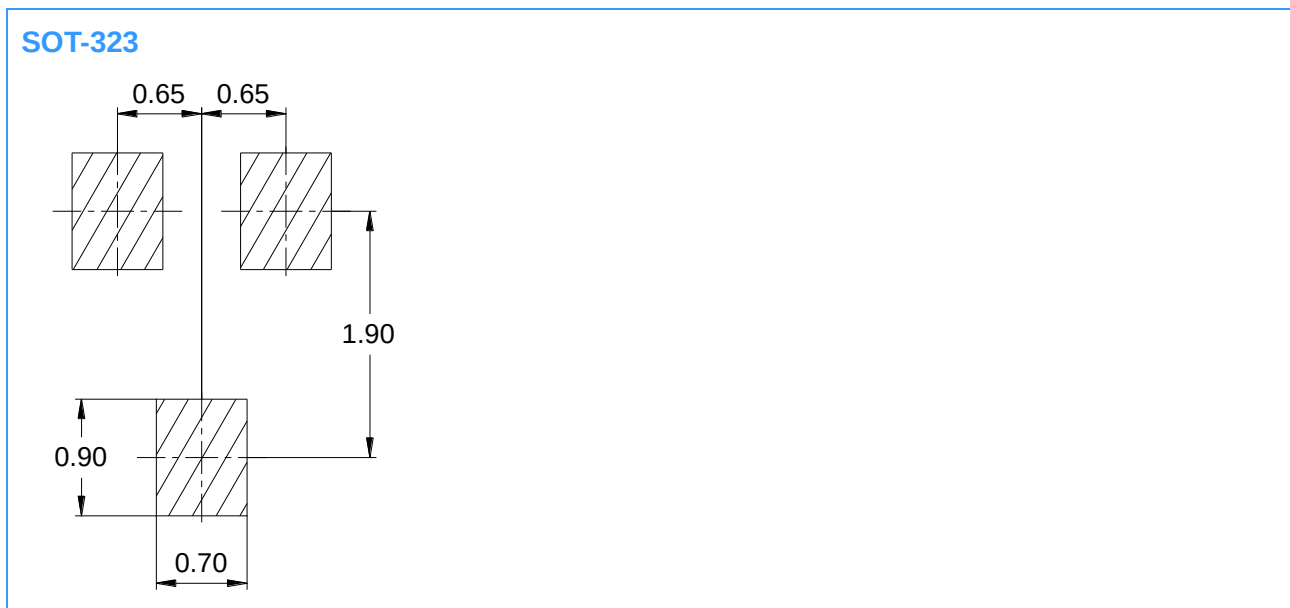


Fig 4 $V_{BE(on)}$ vs. I_C

Package Outline Dimensions (Unit: mm)



Mounting Pad Layout (Unit: mm)



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